Spectroscopic Ellipsometry Focus Topic
Room: 19 - Session EL+TF+AS+EM+SS+PS+EN+NM-MoM

Spectroscopic Ellipsometry for Photovoltaics and Semiconductor Manufacturing
Moderator: M. Creatore, Eindhoven University of Technology, the Netherlands, H. Wormeester, MESA+ Institute for Nanotechnology, Univeristy of Twente, Enschede, The Netherlands

8:20am **EL+TF+AS+EM+SS+PS+EN+NM-MoM1** **Multichannel Spectroscopic Ellipsometry: Applications in I-III-VI$_2$ Thin Film Photovoltaics**, *R.W. Collins, D. Attygalle, P. Aryal, P. Pradhan, N.J. Podraza,* University of Toledo*, V. Ranjan, S. Marsillac,* Old Dominion University **INVITED**
Multichannel spectroscopic ellipsometry (SE) has been applied successfully as an in situ, real time tool for optimizing, monitoring, and controlling multi-stage deposition processes in various thin film photovoltaics (PV) technologies. A particularly challenging process optimization problem involves the thermal co-evaporation of individual elements of Cu, In, Ga, and Se in a three-stage process, which has proven to produce high quality Cu(In$_{1-x}$Ga$_x$)Se$_2$ (CIGS) materials and high performance PV devices. This three-stage process provides a high level of flexibility in determining the phase, composition, and microstructure of the film, but also generates greater challenges in run-to-run reproducibility of the optimized process. Information extracted from real time SE measurements includes the evolution of the bulk layer and one or more surface layer thicknesses, as well as layer dielectric functions. The layer dielectric functions can be analyzed further to extract the phase and alloy compositions and the defect density or grain size, which can assist in understanding the fabrication process, in optimizing solar cells, and ultimately in monitoring and controlling the optimized process for improved reproducibility. In this study, the focus is on analysis of ellipsometric (ψ, Δ) spectra acquired by real time SE in order to characterize (i) the structural and compositional evolution in (In,Ga)$_2$Se$_3$ film growth from In, Ga, and Se fluxes in the first stage, (ii) the transition from Cu-poor to Cu-rich CIGS at the end of the second stage, which occurs under Cu and Se fluxes, and (iii) the transition from Cu-rich to the desired Cu-poor CIGS, which defines the end of the third and final stage, and occurs under a second application of In, Ga, and Se fluxes. After the transition from Cu-poor to Cu-rich material in the second stage, a Cu$_{2-x}$Se phase near the surface of the bulk layer is tracked. In the Cu-rich to Cu-poor transition, this Cu$_{2-x}$Se phase has fully reacted with In, Ga, and Se to form CIGS. Studies using a standard Mo substrate and 2 μm thick CIGS for solar cells have also revealed features in the (ψ, Δ) spectra characteristic of the anticipated changes in the near surface phase composition as established by detailed modeling on thinner and smoother films. Although careful analysis of real time SE is expected to provide quantitative information on the surface properties and their evolution in this case of solar cells, control of the deposition has been successful simply by monitoring real time changes in the ellipsometric (ψ,Δ) spectra.

9:00am **EL+TF+AS+EM+SS+PS+EN+NM-MoM3** **Contribution of Plasma Generated Nanoparticles to the Growth of Microcrystalline Silicon Deposited from SiF$_4$/H$_2$/Argon Gas Mixtures**, *J.-C. Dornstetter, S. Kasouit, J.-F. Besnier,* Total S.a, France*, P. Roca i Cabarrocas,* LPICM-CNRS, Ecole Polytechnique, France
Despite the low fabrication cost of thin film silicon solar modules, this type of technology remains non competitive in main stream markets because of the high BOS costs, due to the low energy conversion efficiency of this type of modules (~10%).We have recently shown that microcrystalline silicon films deposited using SiF$_4$/H$_2$/Argon RF capacitive plasmas have excellent structural and transport properties, compared to films deposited using conventional SiH$_4$/H$_2$ mixtures, allowing for a very good carrier collection, even for thick cells, and Voc values of 0.55 V, without device optimization, thus opening up the path for the realization of high performance solar cells. However, little is known so far about the growth mechanism of this type of materials and the reason for such interesting properties.Studies of silicon thin films deposition from SiF$_4$/H$_2$ mixes, under conditions different from ours, suggested that the growth is due to the deposition of SiF$_2$ radicals, followed by the abstraction of fluorine by hydrogen. Previous work within our group has also shown that deposition occurs only when particles are present in the plasma, and that growth starts from crystallites without any amorphous phase.We present here a systematic study of the growth of

microcrystalline films, together with the composition of nanoparticles attracted by thermophoresis to cold traps located both on the walls of the plasma chamber and in the fore line as a function of deposition conditions. The composition of the deposit on the traps is found to be amorphous at low power/ low hydrogen conditions and becomes crystalline when either of them increases. This correlates well with an increase in atomic hydrogen concentration in the plasma, as estimated by actinometry. The crystalline fraction of the deposited film was measured using in-situ ellipsometry and was found to correlate with the composition of the deposit on the cold traps. Deposition rate is drastically reduced when a water cooled trap is installed on the walls of the plasma chamber, and switches off at high H$_2$ flow rates. Under these conditions, TEM and AFM images, show that at the initial stages of the growth the film is constituted of sparse, hexagonal crystalline particles, having sizes on the order of few tens of nanometers. We interpret the data above as a result of plasma-generated nanocrystals being a significant contribution to the deposited film. This may explain the excellent electronic properties of the films, as the particles are formed in the bulk of the plasma region, free from energetic ions bombardment. We will correlate the structural properties and the film growth mechanisms to the properties of solar cells.

9:20am **EL+TF+AS+EM+SS+PS+EN+NM-MoM4** **Multichannel Spectroscopic Ellipsometry for CdTe Photovoltaics: from Materials and Interfaces to Full-Scale Modules**, *P. Koirala, J. Chen, X. Tan, N.J. Podraza,* The University of Toledo*, S. Marsillac,* Old Dominion University*, R.W. Collins,* The University of Toledo
Real time spectroscopic ellipsometry (RTSE) has been implemented in studies of the evolution of the semiconductor structural and optical properties during sputter deposition of thin film polycrystalline CdS/CdTe solar cells on transparent conducting oxide (TCO) coated glass substrates. Analysis of the real time optical spectra collected during CdS/CdTe deposition requires an optical property database as a function of measurement temperature for all substrate components. These include not only soda lime glass, but also an SiO$_2$ layer and three different SnO$_2$ layers. We report optical functions parameterized versus temperature for the glass substrate and its overlayers starting from room temperature and ending at elevated temperature above which the semiconductor layers are deposited. In fact, such a database has additional applications for on-line, through-the-glass monitoring applications of coated glass at elevated temperature. In the RTSE studies, knowledge of the temperature dependent optical functions of the substrate components enables an accurate substrate temperature determination before the onset of deposition and is critical for accurate extraction of the semiconductor layer optical properties. We implement RTSE to study the filling process of the surface roughness modulations on the top-most SnO$_2$ substrate layer and modification of the optical properties of this layer. This modification is further studied post-deposition by infrared spectroscopic ellipsometry. In addition to providing information on interface formation to the substrate during film growth, RTSE also provides information on the bulk layer CdS growth, its surface roughness evolution, as well as overlying CdTe interface formation and bulk layer growth. Information from RTSE at a single point during solar cell stack deposition assists in the development of a model that can be used for mapping the completed cell stack properties, which can then be correlated with device performance. Independent non-uniformities in the layers over the full area of the cell stack enable optimization of cell performance combinatorially.

9:40am **EL+TF+AS+EM+SS+PS+EN+NM-MoM5** **Determination of Electronic Band Gaps from Optical Spectra**, *R.A. Synowicki,* J.A. Woollam Co., Inc.
The band gap of a material Eg is defined theoretically as the lowest energy for electronic transition from the valence to conduction bands in a solid. For an ideal material free of defects this is the photon energy or wavelength where the optical properties change from transparent to absorbing. However, real materials contain defects which cause absorption to begin below the band gap (i.e. the Urbach Tail) making determination of the true band gap position difficult. For example, in a solar cell the measured absorption edge represents the onset of transitions first due to defects, then from band to band. Empirical methods used to determine the band gap in real materials with defects include the Tauc plot and the Mott-Davis plot. More theoretical mathematical dispersion models such as the Tauc-Lorentz, Cody-Lorentz, and Herzinger-Johs models have been developed which include an adjustable band gap parameter. The various plots and dispersion model methods will be discussed and applied to different materials measured optically via spectroscopic ellipsometry, intensity transmission, reflection, absorption, or a combination of these methods.

10:00am EL+TF+AS+EM+SS+PS+EN+NM-MoM6 Optical Modeling of Plasma-Deposited ZnO: Extended Drude and its Physical Interpretation, *H.C.M. Knoops, M.V. Ponomarev, J.W. Weber, N. Leick, B.W.H. van de Loo, Y.G. Melese, W.M.M. Kessels, M. Creatore*, Eindhoven University of Technology, the Netherlands

High-quality transparent conductive oxides such as ZnO are important due to their electrical and optical properties. To improve these properties the responsible physical processes have to be understood. Traditionally, charge-carrier-scattering processes are investigated by combining morphology data and Hall measurements. This contribution discusses the extensive optical modeling of plasma-deposited ZnO and how its interpretation directly provides insight into the relevant charge-carrier-scattering processes at different length scales. The interpretation is generalized to the concept of frequency-dependent resistivity, which is used to explain the applicability of different Drude models.

Thin films (50-1000 nm) of Al-doped and undoped ZnO were deposited using an expanding thermal plasma MOCVD process.[1] Conditions of high pressure and high diethyl zinc flow allowed for dense films with low electrical resistivities (e.g., 4×10^{-4} Ω cm at 300 nm). The films were analyzed with variable-angle spectroscopic ellipsometry (SE) (0.75 – 5.0 eV), FTIR reflection spectroscopy (0.04 – 0.86 eV), Four-point-probe (FPP), and Hall measurements.

The SE and FTIR data were combined and fitted with classical and extended Drude[2] models. The high intensity of the Drude in the FTIR range resulted in a high sensitivity with which the carrier concentration and mobility could even be determined for thin (~40 nm) undoped ZnO films. An extended Drude model was needed to correctly model the SE energy range, which was explained by the dominance of ionized impurity scattering and a reduction of this scattering for higher photon energies. The grain-boundary-scattering mobility could be determined by the difference between optical and Hall mobilities.[3] When combined with FPP results, the effective mobility can be determined from these optical techniques without the use of Hall measurements. The optical response above the band gap was modeled by a PSEMI or Tauc-Lorentz oscillator model, where a broadening and shift of the transition was seen for increasing carrier concentration.[4]

These insights and a generalized view of electron scattering in ZnO at different length scales will be presented.

1. Ponomarev et al., *J. Appl. Phys.* **Submitted** (2012)

2. Ehrmann and Reineke-Koch, *Thin Solid Films* **519**, 1475 (2010)

3. Steinhauser et al., *Appl. Phys. Lett.* **90**, 142107 (2007)

4. Fujiwara and Kondo, *Phys. Rev. B* **71**, 075109 (2005)

10:40am EL+TF+AS+EM+SS+PS+EN+NM-MoM8 The Ellipsometric Response of Single-Crystal Silicon to Doping, *H.G. Tompkins*, Consultant

The current wisdom is that for ellipsometry in the UV-vis-NIR spectral range, doping of single-crystal silicon can be ignored. We study the ellipsometric response of silicon doped with arsenic at various levels. We also studied the response after implant (before activation) and after the activation (anneal). We find that for samples implanted with 1E18 atoms/cm3, the single-crystal silicon was not amorphized. Implants of 2E19 atoms/cm3 and higher left an amorphous layer on the surface of the wafer the thickness of which was about the depth of the implant. Activation of the sample implanted with 2E19 atoms/cm3 returned the sample to single-crystal silicon and the ellipsometric response in the UV-vis-near_IR is essentially that of undoped silicon. However, the response in the mid-IR is that the extinction coefficient is no longer zero. For samples implanted with 2.5E20 atoms/cm3 and greater, annealing did not return the UV-vis-near_IR ellipsometric response to that of single-crystal silicon. Although this amount of other material (arsenic) is still less that about one tenth of one percent, our conjecture is that the microstructure simply could not be returned to that of a single crystal. As with the lower doped sample, the mid-IR spectral region showed significant increase in the extinction coefficient.

11:00am EL+TF+AS+EM+SS+PS+EN+NM-MoM9 The Effect of Stress on the Optical Properties Semiconductor Films, *A.C. Diebold, G.R. Muthinti, M. Medikonda, T.N. Adam,* College of Nanoscale Science and Engineering, University at Albany, *A. Reznicek, B. Doris*, IBM Research at Albany Nanotech

Here we review the impact of stress on the complex dielectric function of semiconductor films measured using spectroscopic ellipsometry. Two relevant examples of stressed semiconductor layers are pseudomorphic epitaxial layers fabricated during semiconductor manufacturing and strained silicon on insulator (sSOI) wafers. Stress is known to shift the energies of direct gap critical point transitions in semiconductors. The biaxial stress in pseudomorphic films grown on silicon wafers can be as high as that used during opto-elastic studies of bulk semiconductors. The amount of stress in un-relaxed, pseudomorphic films of $Si_{1-x}Ge_x$ on Si (100) reaches 1 GPa for alloys with 20% Ge and is more than 3 GPa for films with > 50% Ge. The bi-axial stress in sSOI is typically ~1 GPa. An elastic theory approach for the effect of strain on the k*p determined band structure and optical transition energy is well known. Both low shear stress and high shear stress approximations can apply to the shift in transition energy depending on the magnitude of the spin orbit splitting energy vs the magnitude of the shear stress. Until recently it was difficult to obtain sets of samples that test both approximations. Here we discuss results from our recent study of pseudomorphic films of $Si_{1-x}Ge_x$ on Si (100) from x= 0.05 to 0.75 which covers both low and high shear regimes. We also present our recent study of the dielectric function of thinned sSOI which illustrates the impact of stress on the optical transitions for the Si layer on sSOI. All of these samples are examples of new materials being used in semiconductor research. The results of this study are directly transferred into cleanroom spectroscopic ellipsometry systems used for process control during manufacturing.

11:20am EL+TF+AS+EM+SS+PS+EN+NM-MoM10 Numerical Ellipsometry: Spectroscopic n-k Plane Analysis of Thin Films Growing on Unknown Layered Substrates, *F.K. Urban, D. Barton*, Florida International University

Spectroscopic ellipsometry measurements on thin films commonly make use of prior knowledge of the structure and optical properties of the underlying substrate. However, imprecision in substrate statistics propagates into the solution for the film of interest. Thus it is more accurate to have a method for solving for film properties which simultaneously obtains whatever is needed about the substrate. And it makes solutions possible whether or not book data or previous substrate solutions are available. In this work we apply Complex Analysis in the n-k plane to achieve solutions employing the well-know reflection equations. The method is carried out at each measured wavelength and does not necessitate an *a-priori* assumption of optical property dependencies on wavelength. The mean square error has been improved by many orders of magnitude, a selected limit of 10^{-14} as opposed to 1 to 30 or so for least squares. Thus the full accuracy of the ellipsometer is now available for more accurate measurements of film thickness and optical properties. The method requires six measurements during growth. The first is used to determine the relationship between Rp and Rs at the film-substrate interface. The following four are used to uniquely determine the values of Rp, Rs, and film n, k, and d. The final measurement confirms the unique solution. Suitability of the model is tested by comparing measurements at two of more wavelengths for self consistency. Results for n and k of the growing film are examined across the measurement spectrum in comparison with parameterizations in common use.

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